Amendments to the Specification:

Please replace the paragraph bridging page 31 and 32, with the following amended paragraph:

After the resist masks are removed, resist masks 434a to 434c are newly formed, and a second doping process is conducted at an acceleration voltage higher than that of the first doping process. Ion doping at this time is conducted under the condition of a dose amount of 1×10^{13} to $1 \times 10^{15}/cm^2$, and an acceleration voltage of 60 to 120 keV. The doping process is conducted using the second conductive layers 428b to 432b as masks with respect to an impurity element such that the impurity element is added to the semiconductor layers below the taper portions of the first conductive layers. Then, a third doping process is conducted at an acceleration voltage lower than that of the second doping process, whereby a state shown in FIG. 9A is obtained. At this time, ion doping is conducted under the condition of a dose amount of 1×10^{15} to $1 \times 10^{17}/cm^2$, and an acceleration voltage of 50 to 100 keV. Due to the second and third doping processes, an impurity element imparting n-type is added to low-concentration impurity regions 436, 442, and 448 overlapped with the first conductive layers in a concentration range of 1×10^{18} to $5 \times 10^{19}/cm$. On the other hand, an impurity element imparting n-type is added to high-concentration impurity regions 435, [[438,]] 441, 444, and 447 in a concentration range of 1×10^{19} to $5 \times 10^{21}/cm^3$.

Please replace the paragraph bridging pages 32 and 33, with the following amended paragraph:

Then, after removing the resist masks 434a to 434c, resist masks 450a to 450c are newly formed, whereby a fourth doping process is conducted. Because of the fourth doping process, impurity regions 453, 454, 459, and 460, in which an impurity element providing a conductivity opposite to the above-mentioned one conductivity type is added, are formed in the semiconductor layers to be active layers of p-channel TFTs.

The second conductive layers ~~428a to 432a~~ 428b to 432b are used as masks with respect to an impurity element, and an impurity element imparting p-type is added, whereby impurity regions are formed in a self-alignment manner. In the present embodiment, the impurity regions 453, 454, 459, and 460 are formed by ion doping using diborane (B_2H_6) (FIG. 9B). During the fourth doping process, the semiconductor layers constituting the n-channel TFTs are covered with the resist masks 450a to 450c. Due to the first to third doping processes, phosphorus is added to the impurity region 439 ~~regions 438 and 439 in different concentrations~~. However, doping is conducted in ~~both the regions~~ the region so that the concentration of an impurity element imparting p-type becomes 1×10^{19} to 5×10^{21} atmos/cm^3, whereby ~~these regions function~~ this region functions as a source region [[and]] or a drain region of a p-channel TFT. Therefore, there is no problem.